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( AND 1 8 2005 E)	First Named Inventor:	Hamza Yilmaz
	Group Art Unit:	2826
INFORMATION DISCLOSUR FIREMENT BY APPLICANT	Examiner Name:	Fetsum Abraham
(Use several sheets if necessary)	Confirmation No.:	3820
	Attorney Docket No.:	YMZ004 US

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Examination Roll

Date Considered:

\* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.

U.S. Department of Commerce, Patent and Trademark Office	Application No.:	Unknown		
	Filing Date:	Unknown		
'' · · · ·	First Named Inventor:	Hamza Yilmaz		
	Group Art Unit:	Unknown		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Examiner Name:	Unknown		
(Use several sheets if necessary)	Confirmation No.:	Unknown		
	Attorney Docket No.:	YMZ004 US		

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